

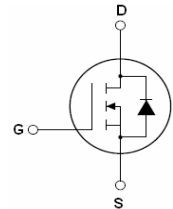
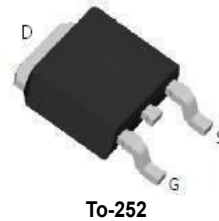
PTD15N10

100V/15A N-Channel Advanced Power MOSFET

Features

- N-Channel, 5V Logic Level Control
- Enhancement mode
- Very low on-resistance @ $V_{GS}=4.5V$
- Fast Switching
- 100% Avalanche test
- Pb-free lead plating; RoHS compliant

V_{DS}	100	V
$R_{DS(on),typ@VGS=10V}$	78	m Ω
$R_{DS(on),typ@VGS=4.5V}$	82	m Ω
I_D	15	A



Maximum ratings, at $T_j=25^\circ C$, unless otherwise specified

Symbol	Parameter	Rating	Unit	
$V_{(BR)DSS}$	Drain-Source breakdown voltage	100	V	
V_{GS}	Gate-Source voltage	± 20	V	
I_D	Continuous drain current@ $V_{GS}=10V$	$T_C=25^\circ C$	15	A
		$T_C=70^\circ C$	9.6	A
I_{DM}	Pulse drain current tested ①	$T_C=25^\circ C$	40	A
P_D	Maximum power dissipation	$T_C=25^\circ C$	30	W
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$	15	A
I_{AS}	Avalanche Current Max	$L=0.5mH$	11	A
E_{AS}	Avalanche energy, single pulsed ②		9	mJ
T_{STG}, T_J	Storage and operating temperature range		-55 to 175	$^\circ C$
Thermal characteristics				
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	60	$^\circ C/W$	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	5	$^\circ C/W$	

Typical Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(Tc=25°C)	V _{DS} =100V, V _{GS} =0V	--	--	1	μA
	Zero Gate Voltage Drain Current(Tc=125°C)	V _{DS} =100V, V _{GS} =0V	--	--	100	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	2.0	3.0	V
R _{DS(ON)}	Drain-Source On-State Resistance ^③	V _{GS} =10V, I _D =10A	--	78	90	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance ^③	V _{GS} =4.5V, I _D =5A	--	82	100	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =30V, V _{GS} =0V, f=1MHz	--	525	--	pF
C _{oss}	Output Capacitance		--	41	--	pF
C _{rss}	Reverse Transfer Capacitance		--	36	--	pF
R _g	Gate Resistance		--	2.6	--	Ω
Q _g	Total Gate Charge	V _{DS} =50V, I _D =3A, V _{GS} =10V	--	15.6	--	nC
Q _{gs}	Gate-Source Charge		--	3.2	--	nC
Q _{gd}	Gate-Drain Charge		--	4.4	--	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =50V, I _D =1A, R _G =6.8Ω, V _{GS} =4.5V	--	8	--	nS
t _r	Turn-on Rise Time		--	4.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	26	--	nS
t _f	Turn-Off Fall Time		--	3.8	--	nS
Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated)						
V _{SD}	Forward on voltage	I _{SD} =10A, V _{GS} =0V	--	0.89	1.20	V
t _{rr}	Reverse Recovery Time	T _J =25°C, I _{sd} =10A, V _{GS} =0V di/dt=500A/μs	--	26	--	nS
Q _{rr}	Reverse Recovery Charge		--	115	--	nC

NOTE:

- ① Repetitive rating; pulse width limited by max. junction temperature
 ② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH, R_G = 25Ω, I_{AS} = 6A, V_{GS} = 10V. Part not recommended for use above this value.
 ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

Typical Characteristics

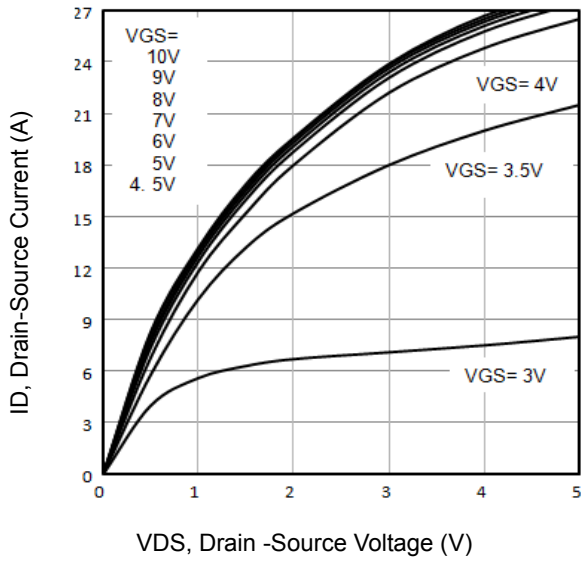


Fig1. Typical Output Characteristics

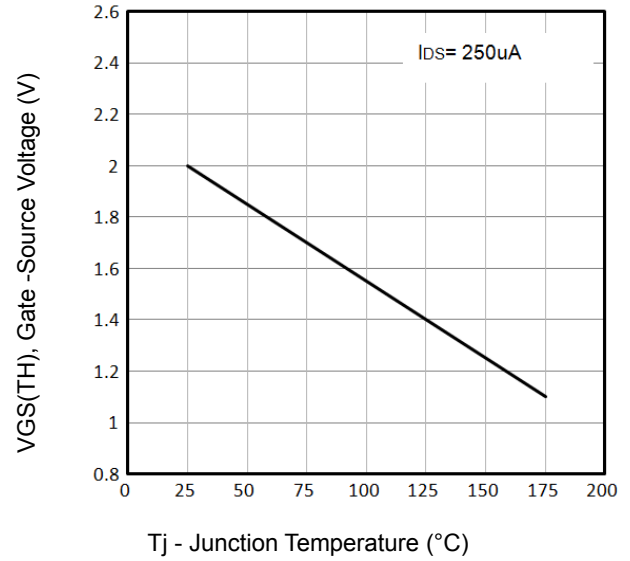


Fig2. $V_{GS(TH)}$ Gate-Source Voltage Vs. T_j

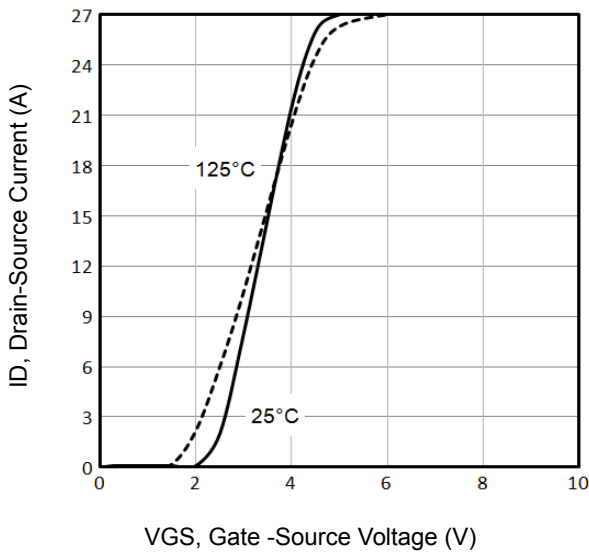


Fig3. Typical Transfer Characteristics

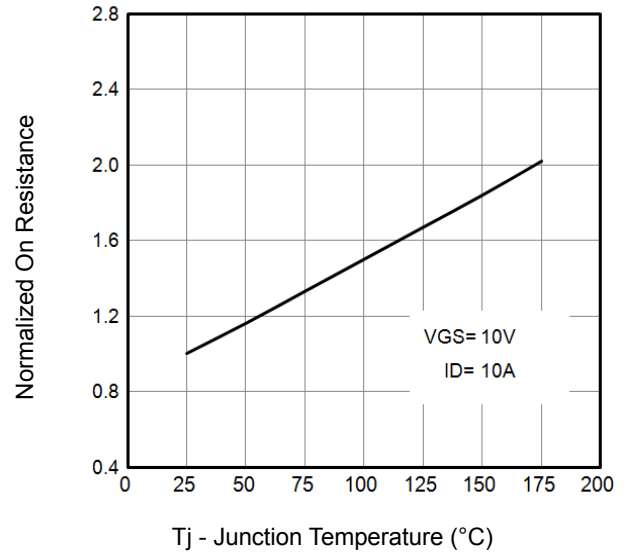


Fig4. Normalized On-Resistance Vs. T_j

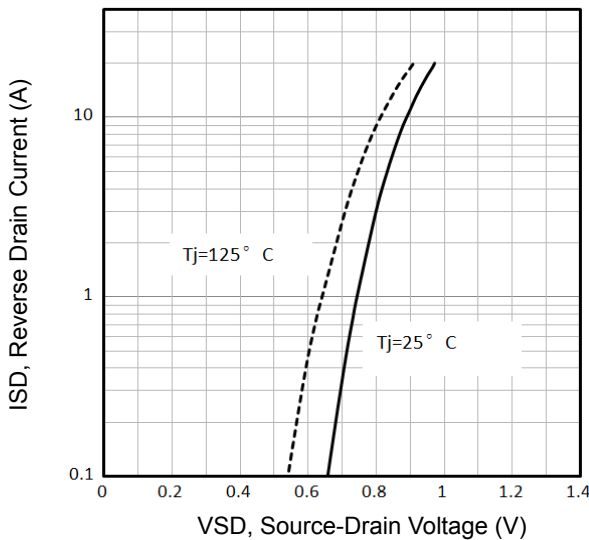


Fig5. Typical Source-Drain Diode Forward Voltage

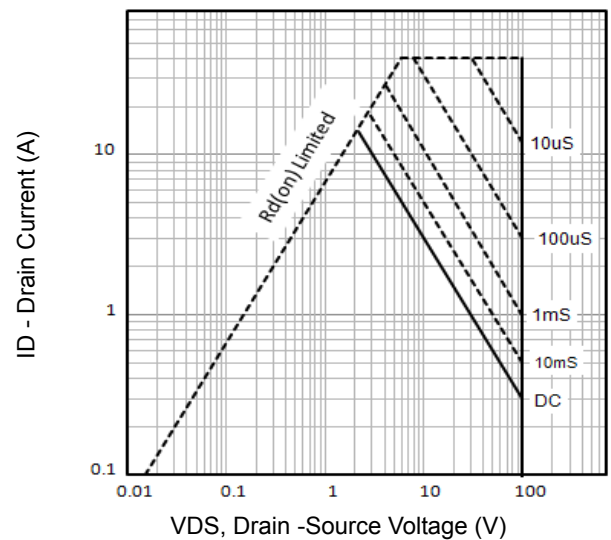


Fig6. Maximum Safe Operating Area

Typical Characteristics

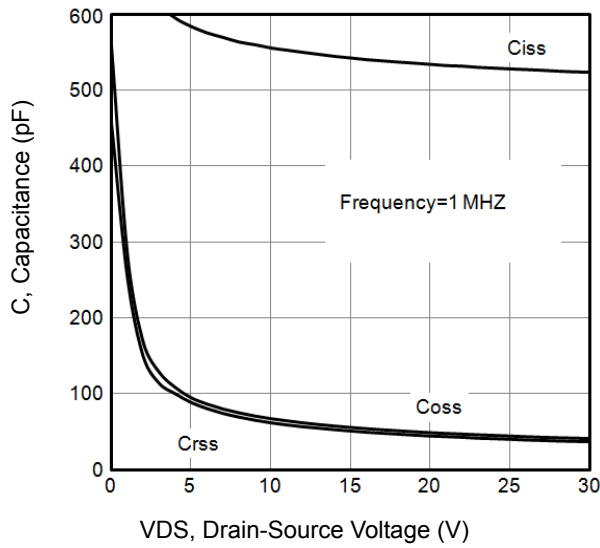


Fig7. Typical Capacitance Vs. Drain-Source Voltage

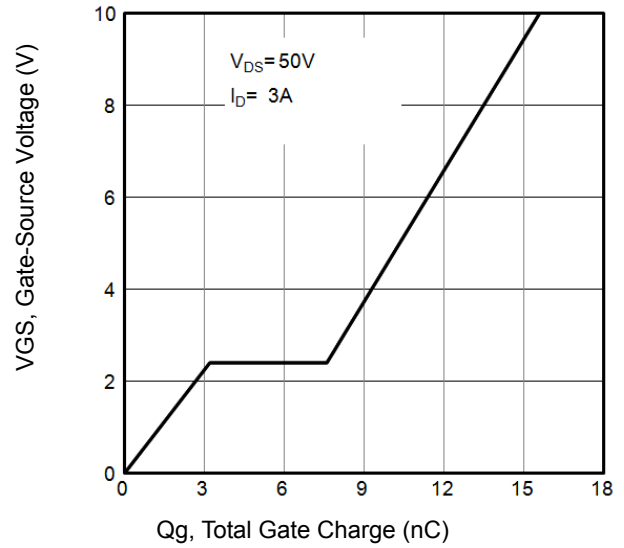


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

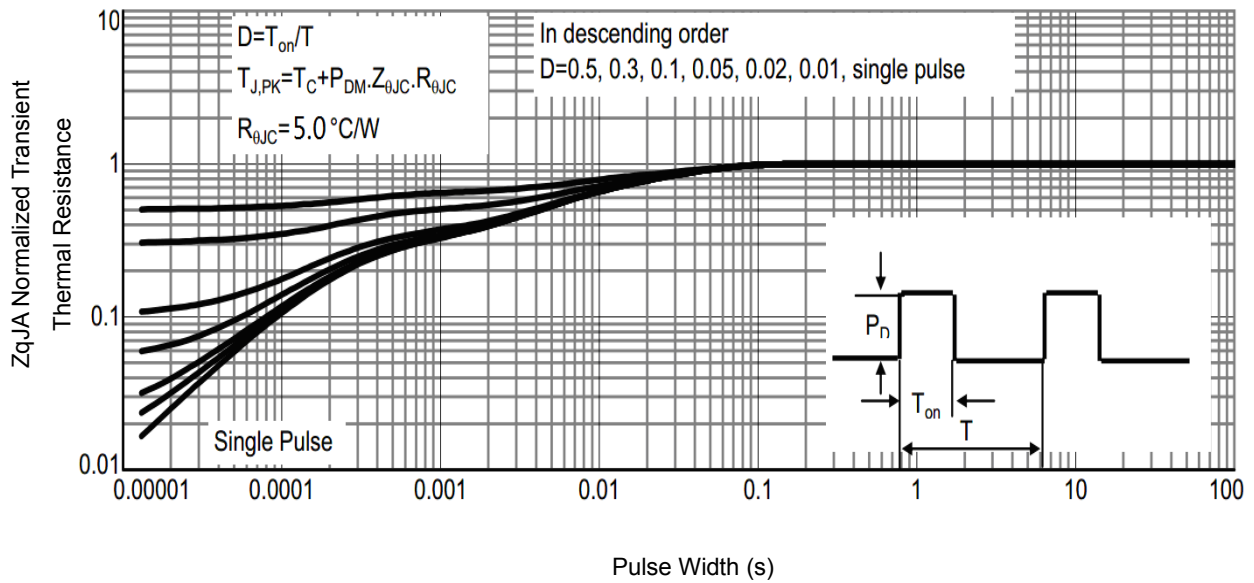


Fig9. Normalized Maximum Transient Thermal Impedance

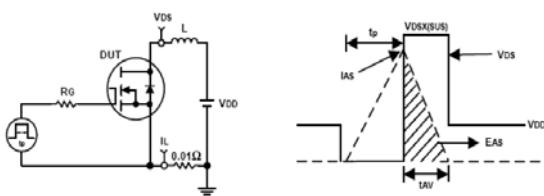


Fig10. Unclamped Inductive Test Circuit and waveforms

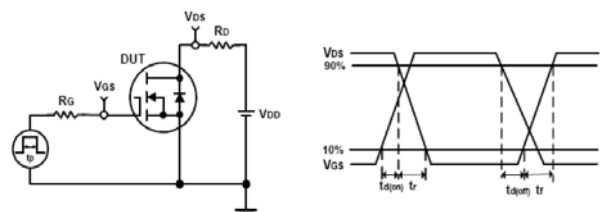


Fig11. Switching Time Test Circuit and waveforms